

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1714	257/e21.214.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L2	844	257/e21.23.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L3	257	257/e21.231.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L4	625	257/e21.237.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L5	364	438/928.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L6	163	438/959.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L7	111	438/963.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52

EAST Search History

L8	914	438/978.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L9	4766	L1 L2 L3 L4 L5 L6 L7 L8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/04 15:52
L10	10	L9 and (dielectric) and (hydrophilic or (silane) or (si near2 H) or (TEOS) or (si near2 N)) and ((hard near2 mask) or (mask near4 (aluminum or al or (titanium near2 nitride) or (ti near2 n) or (tantalum near2 nitride) or (ta near2 n) or (ti near2 si near2 n) or (tungsten near2 nitride) or (w near2 n) or (w near2 si near2 n) or (refractory near2 nitride)))) and (polish or polishing or polished or cmp)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 15:52
S1	133	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic) and (hard adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/03 16:58
S2	83	S1 and (planarization or polish or resurfacing or planar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:07
S3	113	S1 and (planarization or polish or polishing or resurfacing or planar or planarizing or cmp)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 12:51
S4	100	S3 and (cvd or (chemical adj vapor adj deposition) or (spin adj on adj coating) or soc)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:07

EAST Search History

S5	2	S4 and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:07
S6	46	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic near2 layer) and (hard adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 19:01
S7	48	(semiconductor or die or chip or ic or (integrated adj circuit)) and (hydrophilic near2 layer) and (hard adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:03
S8	2	S7 not S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:02
S9	822	(semiconductor or die or chip or ic or (integrated adj circuit)) and (hydrophilic near2 layer) and (mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:06
S10	295	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic near2 layer) and (mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:15

EAST Search History

S11	249	S10 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:03
S12	165	S11 and (planarization or polish or resurfacing or planar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:09
S13	134	S12 and (cvd or (chemical adj vapor adj deposition) or (spin adj on adj coating) or soc)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:04
S14	1	S13 and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:15

EAST Search History

S15	3	S10 and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:06
S16	3	S9 and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 17:06

EAST Search History

S17	163	(semiconductor or die or chip or ic or (integrated adj circuit)) and (planarization or polish or resurfacing or planar) and (cvd or (chemical adj vapor adj deposition) or (spin adj on adj coating) or soc) and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:31
S18	155	S17 and (silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:06
S19	146	S18 and (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:48
S20	88	S19 and (trench or groove or slit or slot)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:51
S21	58	S19 not S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/07 18:07

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S22	557	(semiconductor or die or chip or ic or (integrated adj circuit)) and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:50
S23	494	S22 and (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:08
S24	17	S17 not S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:51
S25	342	S23 not S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:51
S26	65	S25 and damascene	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:58
S27	277	S25 not S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 18:59

EAST Search History

S28	2437	damascene and ((hard adj mask) or (hardmask)) and (dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:01
S29	93	S28 and hydrophilic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 19:00
S30	273	S6 S26 S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:12
S31	52	S29 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:11
S32	29	((hard adj mask) or (hardmask)) and (hydrophilic adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:04
S33	2796	((hard adj mask) or (hardmask)) and ((silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride)or (si near2 n)) adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:08
S34	2630	((hard adj mask) or (hardmask) SAME (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))) and ((silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride)or (si near2 n)) adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:09

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S35	1370	S34 and (planarization or polish or resurfacing or planar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S37	81	S31 S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:11
S38	1330	S35 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:14
S39	1623	S34 and (planarization or polish or polishing or planarizing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:14
S40	1577	S39 not S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:14
S41	0	S40 and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 21:53

EAST Search History

S42	220	S40 and ((organic near3 dielectric) or ((carbon or c) near4 dielectric) or ((carbon or carbide) near2 oxide) or (carbide near4 dielectric) or (c near2 o))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 20:18
S43	867	((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 21:54
S44	106	((organic near3 dielectric) or ((carbon or c) near4 dielectric) or ((carbon or carbide) near2 oxide) or (carbide near4 dielectric) or (c near2 o)) same ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/07 21:55

EAST Search History

S45	36	(sicoh) same ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethylsiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/08 13:06
S46	1	("6737809").PN.	USPAT	OR	OFF	2006/01/08 12:40
S47	1	("6734096").PN.	USPAT	OR	OFF	2006/01/08 13:06
S48	1	("6737747").PN.	USPAT	OR	OFF	2006/06/15 15:56
S49	2911	((hard adj mask) or (hardmask) SAME (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))) and ((silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride) or (si near2 n)) adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:50
S50	1515	S49 and (planarization or polish or resurfacing or planar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:16
S51	320	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic near2 layer) and (mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:50

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S52	152	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic) and (hard adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S53	189	(semiconductor or die or chip or ic or (integrated adj circuit)) and (planarization or polish or resurfacing or planar) and (cvd or (chemical adj vapor adj deposition) or (spin adj on adj coating) or soc) and ((tmcts or 3ms or 4ms or dmdmos or omcts or dems or tmdso or (tetramethyl adj cyclotetra adj siloxane) or (tetramethylcyclotetrasiloxane) or (trimethyl adj silane) or (trimethylsilane) or (tetramethyl adj silane) or (tetramethylsilane) or (dimethyl adj dimethoxy adj silane) or (dimethyldimethoxysilane) or (octamethyl adj cyclotetra adj siloxane) or (octamethylcyclotetrasiloxane) or (diethoxy adj methyl adj silane) or (diethoxymethylsilane) or (tetramethyl adj disiloxane) or (tetramethyldisiloxane)) SAME precursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S54	178	S53 and (silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S55	168	S54 and (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S56	103	S55 and (trench or groove or slit or slot)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/15 17:51

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S57	1515	S49 and (planarization or polish or resurfacing or planar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/15 17:51
S58	183	(semiconductor or die or chip or ic or (integrated adj circuit) or (electronic adj mask)) and (dielectric) and (hydrophilic) and ((hard adj mask) or (hard adj mask))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 12:51
S59	192	(semiconductor or die or chip or ic or (integrated adj circuit) or (electronic adj mask)) and (dielectric) and (hydrophilic) and ((hard adj mask) or (hard adj mask))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 12:51
S60	165	S59 and (planarization or polish or polishing or resurfacing or planar or planarizing or cmp)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 12:53
S61	48	S59 and ((planarization or polish or polishing or resurfacing or planar or planarizing or cmp) same (side or bevel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 12:53
S62	52	((semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic near2 layer) and (mask)) and @pd>"20060615"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:15
S63	3233	((hard adj mask) or (hardmask) SAME (aluminum or al or tin or (titanium adj nitride) or (tantalum adj nitride) or tan or (titanium adj silicon adj nitride) or tisin or (tungsten adj nitride) or wn or (tungsten adj silicon adj nitride) or (wsin) or (refractory adj nitride))) and ((silane or (siH) or tatraethylorthosilicateoxide or (tertaethyl adj ortho adj silicate adj oxide) or (teos) or sin or (silicon adj nitride) or (si near2 n)) adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:16

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S64	167	(S63 and (planarization or polish or resurfacing or planar)) and @pd>"20060615"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:17
S65	218	S62 S64	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:17
S66	192	(semiconductor or die or chip or ic or (integrated adj circuit) or (electronic adj mask)) and (dielectric) and (hydrophilic) and ((hard adj mask) or (hard adj mask))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:17
S67	48	S66 and ((planarization or polish or polishing or resurfacing or planar or planarizing or cmp) same (side or bevel))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:17
S68	216	S65 not S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:35
S69	2	("20060006545").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:35
S70	2729	257/774.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:35
S71	3990	257/758.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:55

EAST Search History

S72	422	257/642.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:35
S73	987	438/629.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:36
S74	2861	438/622.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:36
S75	1019	438/725.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:36
S76	1691	257/e21.214.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:55
S77	769	257/e21.23.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:55
S78	252	257/e21.231.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:55

EAST Search History

S79	568	257/e21.237.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:55
S80	360	438/928.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:56
S81	161	438/959.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:56
S82	109	438/963.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:56
S83	912	438/978.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:56
S84	4616	S76 S77 S78 S79 S80 S81 S82 S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/14 14:57
S85	61	S84 and bevel	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 14:58

EAST Search History

S86	79	S84 and hydrophilic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 15:04
S87	69	S84 and ((hard adj mask) or hardmask)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 15:05
S88	65	S87 not S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 15:05
S89	65	S88 not S86	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 15:05
S90	62	S88 not S85	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/14 15:05
S91	749	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic or (silane) or (si near2 H) or (TEOS) or (si near2 N)) and ((hard near2 mask) or (mask near4 (aluminum or al or (titanium near2 nitride) or (ti near2 n) or (tantalum near2 nitride) or (ta near2 n) or (ti near2 si near2 n) or (tungsten near2 nitride) or (w near2 n) or (w near2 si near2 n) or (refractory near2 nitride)))) and ((polish or polishing or polished or cmp) same (bevel or edge or side))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/03 17:14

EAST Search History

S92	432	(semiconductor or die or chip or ic or (integrated adj circuit)) and (dielectric) and (hydrophilic or (silane) or (si near2 H) or (TEOS) or (si near2 N)) and ((hard near2 mask) or (mask near4 (aluminum or al or (titanium near2 nitride) or (ti near2 n) or (tantalum near2 nitride) or (ta near2 n) or (ti near2 si near2 n) or (tungsten near2 nitride) or (w near2 n) or (w near2 si near2 n) or (refractory near2 nitride)))) and ((polish or polishing or polished or cmp) with (bevel or edge or side))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/03 17:15
S93	432	(semiconductor or die or chip or ic or (integrated adj circuit) or (electronic adj device)) and (dielectric) and (hydrophilic or (silane) or (si near2 H) or (TEOS) or (si near2 N)) and ((hard near2 mask) or (mask near4 (aluminum or al or (titanium near2 nitride) or (ti near2 n) or (tantalum near2 nitride) or (ta near2 n) or (ti near2 si near2 n) or (tungsten near2 nitride) or (w near2 n) or (w near2 si near2 n) or (refractory near2 nitride)))) and ((polish or polishing or polished or cmp) with (bevel or edge or side))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/04 15:52
S94	55	(semiconductor or die or chip or ic or (integrated adj circuit) or (electronic adj device)) and (dielectric) and (hydrophilic or (silane) or (si near2 H) or (TEOS) or (si near2 N)) and ((hard near2 mask) or (mask near4 (aluminum or al or (titanium near2 nitride) or (ti near2 n) or (tantalum near2 nitride) or (ta near2 n) or (ti near2 si near2 n) or (tungsten near2 nitride) or (w near2 n) or (w near2 si near2 n) or (refractory near2 nitride)))) and ((polish or polishing or polished or cmp) near5 (side))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/03 18:23